



DMG1012T

### N-CHANNEL ENHANCEMENT MODE MOSFET

### **Features**

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected up to 2kV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

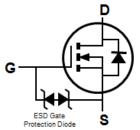
### **Mechanical Data**

- Case: SOT523
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Alloy 42
  Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram
- Weight: 0.002 grams (Approximate)



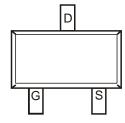
Top View

SOT523



Equivalent Circuit

(Note 6)



Top View

### Ordering Information (Note 5)

	Part Number	Qualification	Case	Packaging				
	DMG1012T-7	Commercial	SOT523	3000/Tape & Reel				
	DMG1012T-13 Commercial		SOT523	10000/Tape & Reel				
	DMG1012TQ-7	Automotive	SOT523	3000/Tape & Reel				
Notes:	s: 1 No purposely added lead Fully FU Directive 2002/95/FC (RoHS) 2011/65/FU (RoHS 2) & 2015/863/FU (RoHS 3) compliant							

No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

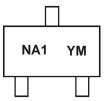
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <100ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to https://www.diodes.com/quality/.

5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

6. The ESD gate protection diode is only designed to protect against ESD events. No gate-source voltage greater than the maximum V<sub>GSS</sub> rating (given on page 2) can be applied.

### **Marking Information**



NA1 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: F = 2018) M = Month (ex: 9 = September)

Date Code Key

Year	2009		2018	2019	202	20 20	21 2	2022	2023	2024	2025	2026
Code	W		F	G	Н			J	K	L	М	Ν
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	4	0	0	4	-	C	7	0	0	0	N	



# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteris	tic		Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	20	V
Gate-Source Voltage			V <sub>GSS</sub>	±6	V
Continuous Drain Current (Note 7)Steady State $T_A = +25^{\circ}C$ $T_A = +85^{\circ}C$			ID	0.63 0.45	A
Pulsed Drain Current			I <sub>DM</sub>	6	А

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 7)	PD	0.28	W
Thermal Resistance, Junction to Ambient (Note 7)	R <sub>θJA</sub>	452	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C

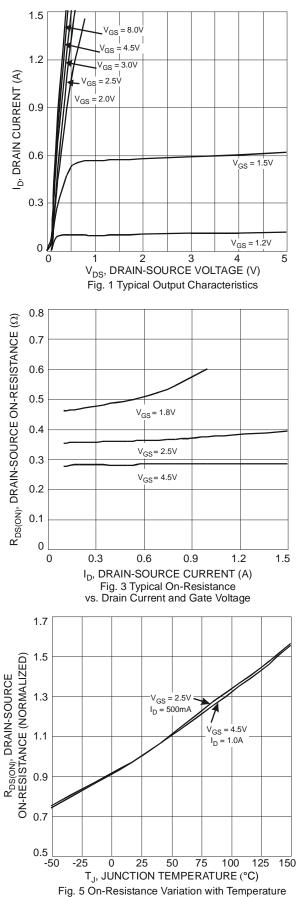
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

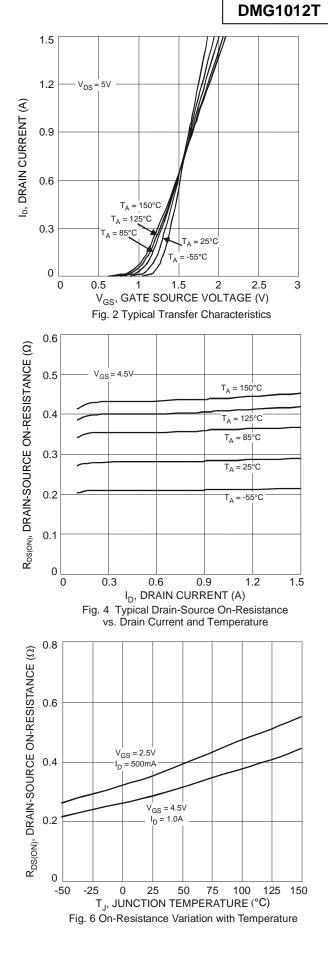
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	_	_	V	$V_{GS} = 0V, I_D = 250 \mu A$	
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>		—	100	nA	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	—	±1.0	μA	$V_{GS} = \pm 4.5 V, V_{DS} = 0 V$	
ON CHARACTERISTICS (Note 8)						-	
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.5	_	1.0	V	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$	
		_	0.3	0.4		$V_{GS} = 4.5V, I_D = 600mA$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>		0.4	0.5	Ω	$V_{GS} = 2.5V, I_D = 500mA$	
			0.5	0.7		V <sub>GS</sub> = 1.8V, I <sub>D</sub> = 350mA	
Forward Transfer Admittance	Y <sub>fs</sub>	_	1.4	_	S	$V_{DS} = 10V, I_D = 400mA$	
Diode Forward Voltage	V <sub>SD</sub>	_	0.7	1.2	V	$V_{GS} = 0V, I_{S} = 150mA$	
DYNAMIC CHARACTERISTICS (Note 9)						-	
Input Capacitance	Ciss		60.67	_	pF		
Output Capacitance	Coss	_	9.68		pF	$V_{DS} = 16V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	5.37	—	pF		
Total Gate Charge	Qq	_	736.6	_	рС		
Gate-Source Charge	Q <sub>qs</sub>	—	93.6	—	рС	$V_{GS} = 4.5V, V_{DS} = 10V,$	
Gate-Drain Charge	Q <sub>gd</sub>	_	116.6	—	рС	$I_D = 250 \text{mA}$	
Turn-On Delay Time	t <sub>D(ON)</sub>		5.1		ns		
Turn-On Rise Time	t <sub>R</sub>		7.4	—	ns	$V_{DD} = 10V, V_{GS} = 4.5V,$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>		26.7	—	ns	$R_{L} = 47\Omega, R_{G} = 10\Omega,$	
Turn-Off Fall Time	t <sub>F</sub>	_	12.3	—	ns	$-I_D = 200 \text{mA}$	

Notes: 7. Device mounted on FR-4 PCB, with minimum recommended pad layout.

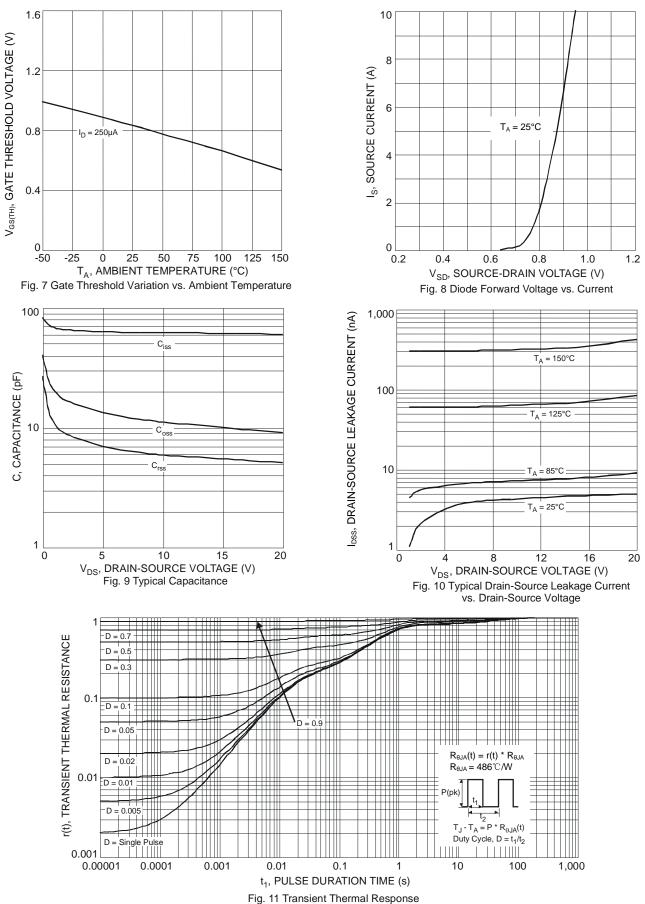
Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.









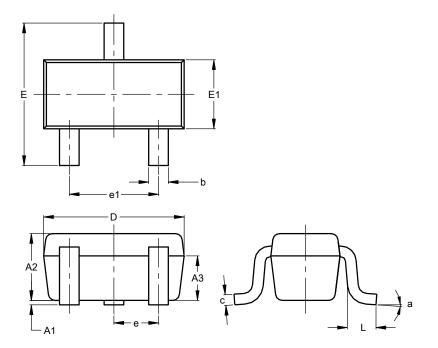




# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT523

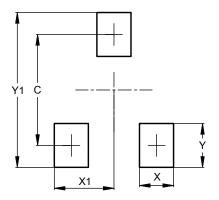


	50	DT523							
DIM	IVIIN	wax	Тур						
A1	0.00	0.10	0.05						
A2	0.60	0.80	0.75						
A3	0.45	0.65	0.50						
b	0.15	0.30	0.22						
С	0.10	0.20	0.12						
D	1.50	1.70	1.60						
<b>E</b> 1.45		1.75	1.60						
<b>E1</b> 0.75		0.85	0.80						
е	0.50 BSC								
e1	0.90	1.10	1.00						
L	0.20	0.40	0.33						
а	0°		8°						
Α	I Dimen	sions ir	n mm						

## Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT523



Dimensions	Value (in mm)
С	1.29
Х	0.40
X1	0.70
Y	0.51
Y1	1.80



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